

NPN RF POWER TRANSISTOR

DESCRIPTION:

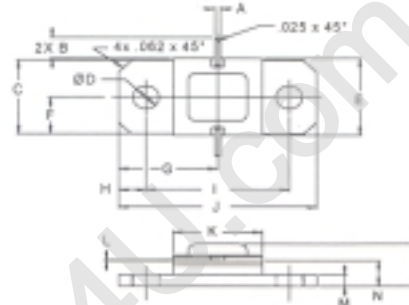
The **ASI TAN75A** is a Common Base Transistor Designed for TACAN Pulse Power Amplifier Applications.

FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

MAXIMUM RATINGS

I_C	9.0 A
BV_{CES}	55 V
BV_{EBO}	4.0 V
P_{DISS}	290 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.60 °C/W

PACKAGE STYLE .400 2NL FLG


DIM	MINIMUM Inches / mm	MAXIMUM Inches / mm
A	.020 / 0.51	.030 / 0.76
B	.180 / 2.54	
C	.375 / 9.53	.395 / 10.03
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F		.193 / 4.90
G		.450 / 11.43
H		.125 / 3.18
I	.640 / 16.26	.660 / 16.76
J	.690 / 22.51	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.084 / 0.10	.097 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.115 / 3.00	.131 / 3.33
P		.230 / 5.84

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 15 mA	50			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	5.0		100	
P_{OUT} P_G η_C VSRW	V _{CC} = 50 V P _{IN} = 12 W f = 960 to 1215 MHz Pulse Width = 20 μS Duty Cycle = 5 %	75	80 8.5 40 ∞ :1		W dB %